

## ABSTRACT

A Ge-Cr alloy sputtering target containing 5 to 50at% of Cr and having a relative density of 95% or more, and a manufacturing method of such a Ge-Cr alloy sputtering target wherein Cr powder having a minus sieve of  $75\mu\text{m}$  or less, and Ge powder having a minus sieve of  $250\mu\text{m}$  or less and having a BET specific surface area of  $0.4\text{m}^2/\text{g}$  or less are dispersively mixed in an even manner, and sintered thereafter.

Thereby provided is a Ge-Cr alloy sputtering target capable of suppressing variation of the deposition speed and film composition, as well as improving the production yield, of the GeCrN layer deposited with reactive sputtering as the intermediate layer between the recording layer and protective layer of a phase-change optical disk, and the manufacturing method of such a target.